OPA9455

Infrared LED Chip

GaAs /GaAs

1.Material

Substrate	GaAs	(N Type)
Epitaxial Layer	GaAs	(P/N Type)

2.Electrode

N (Cathode) Side Gold Alloy
P (Anode) Side Gold Alloy

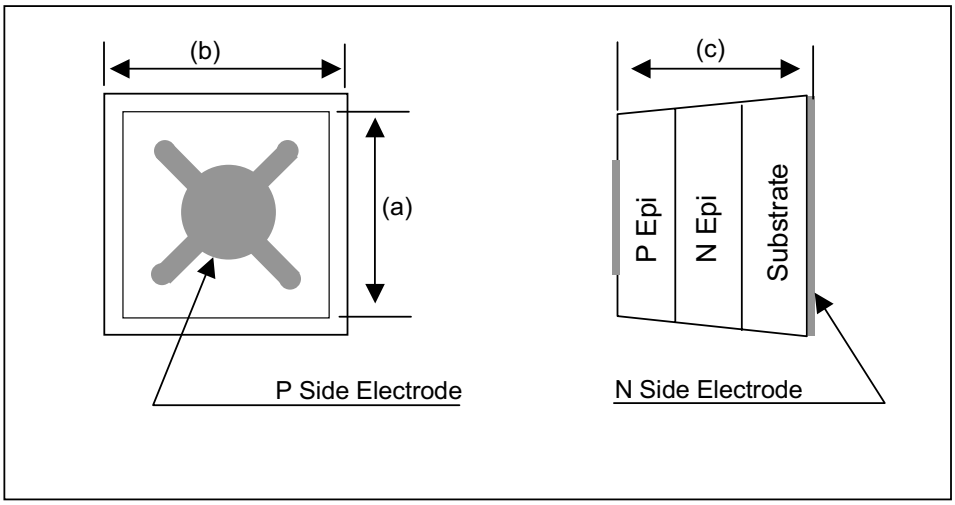
3. Electro-Optical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Forward Voltage	$V_{F(1)}$		1.2		V	I_F=20㎃
	$V_{F(2)}$		1.4	1.7	V	I_F=100㎃
Reverse Voltage	V_R	5.0	30		V	I_R=10㎂
Power	$P_{O(1)}$		4		mW	I_F=20㎃
	$P_{O(2)}$	7	13		mW	I_F=100㎃
Wavelength	λ_P		940		nm	I_F=20㎃
	$\Delta\lambda$		45		nm	I_F=20㎃

Note : Assembled into T1$^3/_4$ plastic package.

4. Mechanical Data

(a) Emission Area ---------- 11mil × 11mil
(b) Bottom Area ---------- 13mil × 13mil
(c) Chip Thickness ---------- 11mil



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